

1A, 200V-1000V High Efficient Surface Mount Rectifier

FEATURES

- · Glass passivated junction chip
- Ideal for automated placement
- Low reverse leakage
- Moisture sensitivity level: level 1, per J-STD-020
- Compliant to RoHS directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

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- Switch Mode Power Supply
- Inverters and Converters
- Free Wheeling diodes

MECHANICAL DATA

Case: SMAF

• Molding compound meets UL 94V-0 flammability rating

• Terminal: Matte tin plated leads, solderable per J-STD-002

Meet JESD 201 class 1 whisker test

· Polarity: Indicated by cathode band

• Weight: 0.035 g (approximately)

KEY PARAMETERS				
PARAMETER	VALUE	UNIT		
I _F	1	Α		
V_{RRM}	200-1000	V		
I _{FSM}	30	Α		
T _{J MAX}	150	°C		
Package	SMAF			









SMAF



ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)								
PARAMETER		SYMBOL	HS1D F-T	HS1G F-T	HS1J F-T	HS1K F-T	HS1M F-T	UNIT
Marking code on the dev	vice		HS1DF	HS1GF	HS1JF	HS1KF	HS1MF	
Repetitive peak reverse	voltage	V_{RRM}	200	400	600	800	1000	V
Reverse voltage, total rn	ns value	$V_{R(RMS)}$	140	280	420	560	700	V
DC blocking voltage	DC blocking voltage		200	400	600	800	1000	V
Forward current	Forward current		1				Α	
Surge peak forward current single half sine-	8.3 ms at $T_A = 25^{\circ}C$				30			А
wave superimposed on rated load	1.0 ms at T_A = 25°C	I _{FSM}	90					Α
Junction temperature		TJ	-55 to +150				°C	
Storage temperature		T _{STG}	-55 to +150				°C	





THERMAL PERFORMANCE					
PARAMETER	SYMBOL	TYP	UNIT		
Junction-to-lead thermal resistance	R _{OJL}	15	°C/W		
Junction-to-ambient thermal resistance	R _{OJA}	89	°C/W		
Junction-to-case thermal resistance	R _{eJC}	22	°C/W		

Thermal Performance Note: Units mounted on PCB (5mm x 5mm Cu pad test board)

ELECTRICAL SPECIF PARAMETE	CONDITIONS	SYMBOL	TYP	MAX	UNIT	
		I _F = 0.5A, T _J = 25°C		0.80	-	V
		I _F = 1A, T _J = 25°C		0.86	1.0	V
	HS1DF-T	I _F = 0.5A, T _J = 125°C		0.65	-	V
		I _F = 1A, T _J = 125°C		0.73	0.82	V
		I _F = 0.5A, T _J = 25°C		0.87	-	V
- (1)	11040F T	I _F = 1A, T _J = 25°C	1	0.95	1.4	V
Forward voltage ⁽¹⁾	HS1GF-T	I _F = 0.5A, T _J = 125°C	V _F	0.70	-	V
		I _F = 1A, T _J = 125°C		0.79	0.94	V
		I _F = 0.5A, T _J = 25°C		1.12	-	V
	HS1JF-T	I _F = 1A, T _J = 25°C		1.23	1.7	V
	HS1KF-T HS1MF-T	I _F = 0.5A, T _J = 125°C		0.90	-	V
		I _F = 1A, T _J = 125°C		1.02	1.27	V
Doverge gurrent @ reted V (2)	T _J = 25°C		-	5	μA
Reverse current @ rated V _R ⁽²⁾		T _J = 125°C	- I _R	-	125	μΑ
	HS1DF-T HS1GF-T	1 0501 400	t _{rr}	-	50	ns
Reverse recovery time	HS1JF-T HS1KF-T HS1MF-T	− I _F =0.5A,I _R =1.0A, Irr=0.25A		-	75	ns
	HS1DF-T		CJ	19	-	pF
lunation conscitance	HS1GF-T	1 MH= \/ 4 O\/		11	-	pF
Junction capacitance	HS1JF-T HS1KF-T HS1MF-T	1 MHz, V _R =4.0V		8	-	pF

Notes:

- (1) Pulse test with PW=0.3 ms
- (2) Pulse test with PW=30 ms

ORDERING INFORMATION					
ORDERING CODE	PACKAGE	PACKING			
HS1XF-T R3G ⁽¹⁾	SMAF	1,800 / 7" Plastic reel			
HS1XF-T M2G ⁽¹⁾	SMAF	7,500 / 13" Plastic reel			
HS1XF-T R2G ⁽¹⁾	SMAF	7,500 / 13" Paper reel			

Notes:

(1) "X" defines voltage from 200V(HS1DF-T) to 1000V(HS1MF-T)



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Fig.1 Forward Current Derating Curve

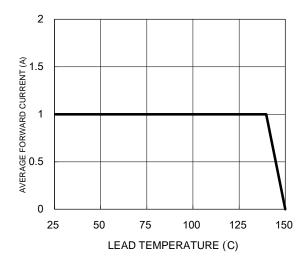


Fig.3 Typical Reverse Characteristics

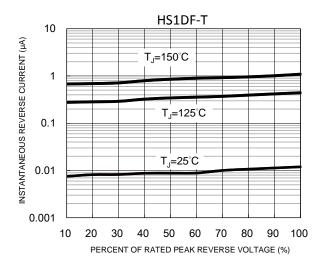


Fig.5 Typical Reverse Characteristics

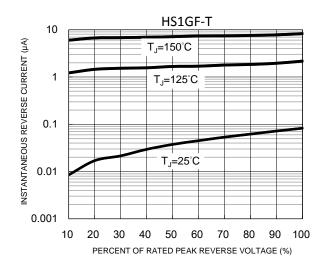


Fig.2 Typical Junction Capacitance

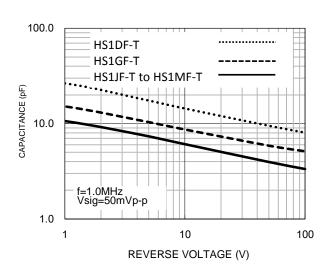


Fig.4 Typical Forward Characteristics

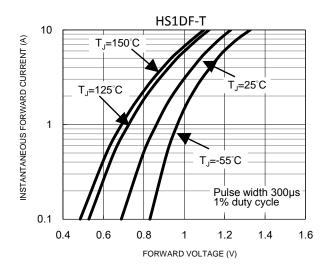
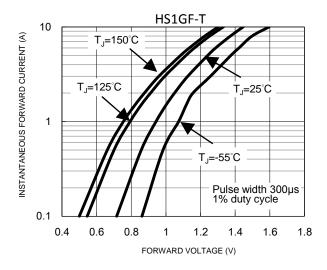


Fig.6 Typical Forward Characteristics



3



Fig.7 Typical Reverse Characteristics

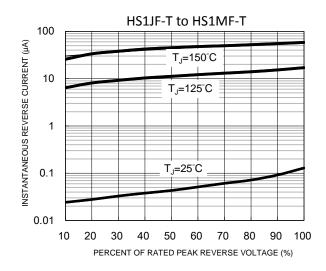


Fig.8 Typical Forward Characteristics

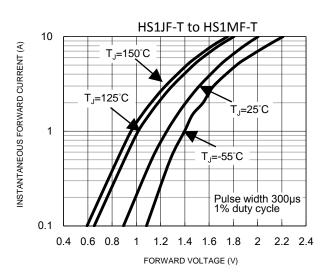
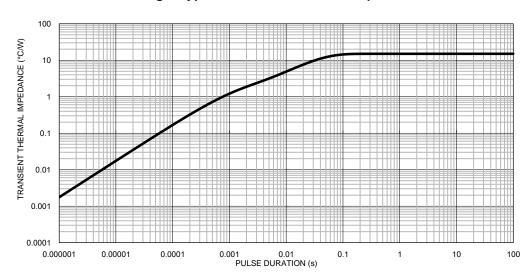


Fig.9 Typical Transient Thermal Impedance

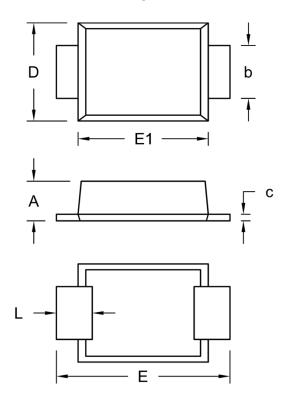


4



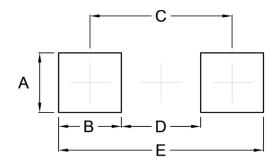
PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

SMAF



DIM.	Unit	(mm)	Unit (inch)		
Dilvi.	Min.	Max.	Min.	Max.	
А	1.00	1.10	0.039	0.043	
b	1.30	1.50	0.051	0.059	
С	0.10	0.25	0.004	0.010	
D	2.40	2.80	0.094	0.110	
E	4.40	4.80	0.173	0.189	
E1	3.25	3.65	0.128	0.144	
L	0.70	1.20	0.028	0.047	

SUGGESTED PAD LAYOUT



Symbol	Unit (mm)	Unit (inch)
Α	1.57	0.062
В	1.66	0.065
С	3.76	0.148
D	2.10	0.083
E	5.42	0.213

MARKING DIAGRAM



P/N = Marking Code
G = Green Compound
YW = Date Code
F = Factory Code



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6